

EAST - [10604190b.wsp:1]

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L1: (1) "20040262784"
 L2: (1) ("6806584").PH.
 L3: (1) ("6825529").PH.
 L4: (1) "20040262784"
 L5: (378) spacer\$1 and field near effect near transistor\$1 and first near width
 L7: (5) 5 and 6
 L6: (593) spacer\$1 and compressive near stress and tensile near stress

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spacer\$1 and compressive near stress and tensile near stress

| | U | I | Document ID | Issue Date | Pages | Title | Current OR | Current XRef | |
|----|-------------------------------------|--------------------------|-------------------|------------|-------|---|------------|---------------------|--|
| 1 | <input type="checkbox"/> | <input type="checkbox"/> | US 20050121745 A1 | 20050609 | 11 | Method of improving the top plate electrode stress inducing voids for 1T1RAM process | 257/532 | 438/636 | |
| 2 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 20050119770 A1 | 20050602 | | Method for introducing hydrogen into a channel region of a metal oxide semiconductor (MOS) device | 438/305 | 438/38; 436/958 | |
| 3 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 20050116360 A1 | 20050602 | | Complementary field-effect transistors and methods of manufacture | | 257/900 | |
| 4 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 20050116294 A1 | 20050602 | | Semiconductor device and method for manufacturing the same | 257/351 | 257/353; 257/354 | |
| 5 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 20050112817 A1 | 20050526 | 32 | Semiconductor device having high drive current and method of manufacture thereof | 438/219 | 257/374 | |
| 6 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 20050110082 A1 | 20050526 | | Semiconductor device having high drive current and method of manufacture therefor | 257/341 | | |
| 7 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 20050110043 A1 | 20050526 | | Nitride semiconductor substrate, method of fabrication thereof, and semiconductor element built thereon | 257/194 | | |
| 8 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 20050106898 A1 | 20050519 | | Silicon nitride film and semiconductor device, and manufacturing method thereof | 438/792 | | |
| 9 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 20050106810 A1 | 20050519 | | Stress assisted current driven switching for magnetic memory applications | 438/257 | | |
| 10 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 20050106799 A1 | 20050519 | | STRESSED SEMICONDUCTOR DEVICE STRUCTURES HAVING GRANULAR SEMICONDUCTOR MATERIAL | 438/199 | | |
| 11 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 20050104922 A1 | 20050519 | | Inkjet printhead with integral nozzle plate | 347/20 | | |